

S10 5	1272	((438/157) or (438/283) or (438/304) or (438/596) or (438/696)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/09 19:35
S10 6	364	finfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:26
S10 7	138	fin near fet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:26
S10 8	217081	mosfet or (metal adj (oxide or insulat\$4) adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:26
S10 9	38	fin near S108	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:26
S11 0	458	S106 or S107 or S109	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:26
S11 1	92	amd.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:26
S11 2	18061	(advanced adj micro\$4).as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:27
S11 3	18139	S111 or S112	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:27
S11 4	113	S113 and S110	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:29

S11 5	140969	fin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:29
S11 6	140969	fin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:29
S11 7	22435	(S110 or S116).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:30
S11 8	46	S113 and S117	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 13:30
S11 9	113	S117 and S110	US-PGPUB	OR	ON	2005/06/10 13:32